

Low voltage NPN power transistor

Features

- Low collector-emitter saturation voltage
- Fast switching speed

Applications

- Power amplifier
- Switching circuits

Description

This device is an NPN transistor manufactured using new low voltage planar technology with double metal process. The result is a transistor which boasts exceptionally high gain performance coupled with very low saturation voltage.

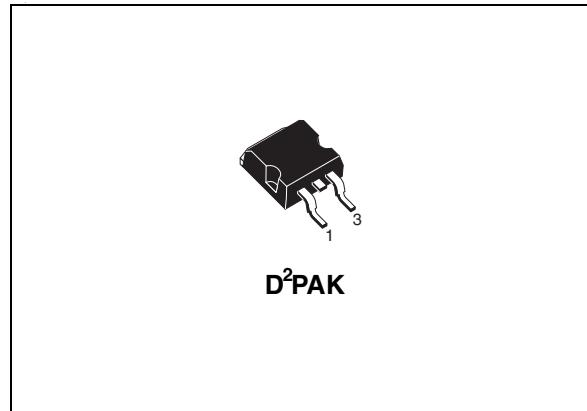


Figure 1. Internal schematic diagram

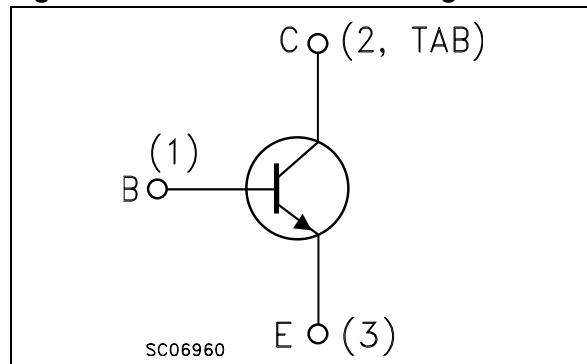


Table 1. Device summary

Order codes	Marking	Package	Packaging
MJB44H11T4	MJB44H11	D ² PAK	Tape and reel

1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	80	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	5	V
I_C	Collector current	10	A
I_{CM}	Collector peak current	20	A
P_{TOT}	Total dissipation at $T_{case} = 25^\circ\text{C}$	50	W
T_{STG}	Storage temperature	-55 to 150	$^\circ\text{C}$
T_J	Max. operating junction temperature	150	$^\circ\text{C}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case max	2.5	$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

$T_{case} = 25^\circ\text{C}$; unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{CEO(sus)}^{(1)}$	Collector-emitter sustaining voltage ($I_B = 0$)	$I_C = 30 \text{ mA}$	80	-		V
I_{CES}	Collector cut-off current ($V_{BE} = 0$)	$V_{CE} = 80 \text{ V}$		-	10	μA
I_{EBO}	Emitter cut-off current ($I_C = 0$)	$V_{EB} = 5 \text{ V}$		-	50	μA
$V_{CE(sat)}^{(1)}$	Collector-emitter saturation voltage	$I_C = 8 \text{ A}$ $I_B = 0.4 \text{ A}$		-	1	V
$V_{BE(sat)}^{(1)}$	Base-emitter saturation voltage	$I_C = 8 \text{ A}$ $I_B = 0.8 \text{ A}$		-	1.5	V
$h_{FE}^{(1)}$	DC current gain	$I_C = 2 \text{ A}$ $V_{CE} = 1 \text{ V}$	60	-		
		$I_C = 4 \text{ A}$ $V_{CE} = 1 \text{ V}$	40	-		

1. Pulse test: pulse duration $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

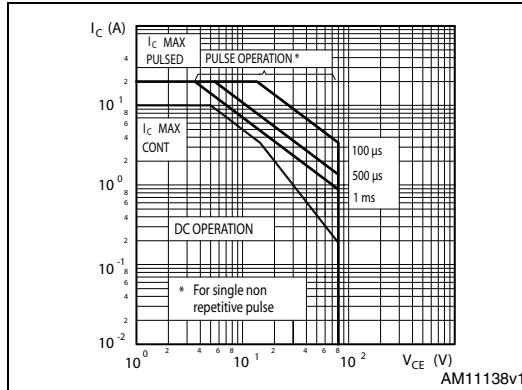


Figure 3. Derating curve

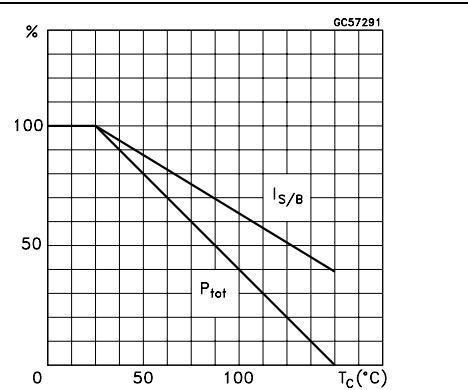


Figure 4. DC current gain

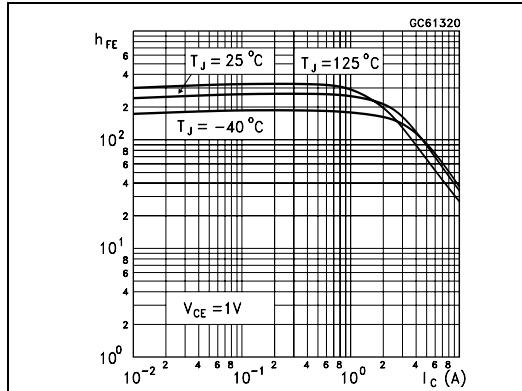
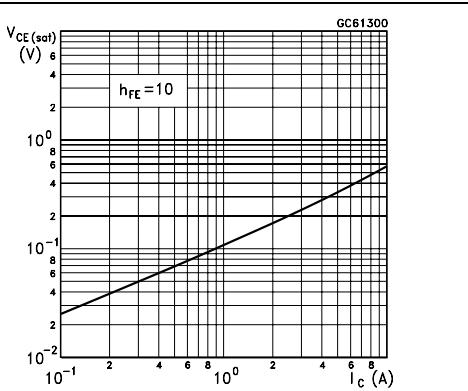


Figure 5. Collector-emitter saturation voltage

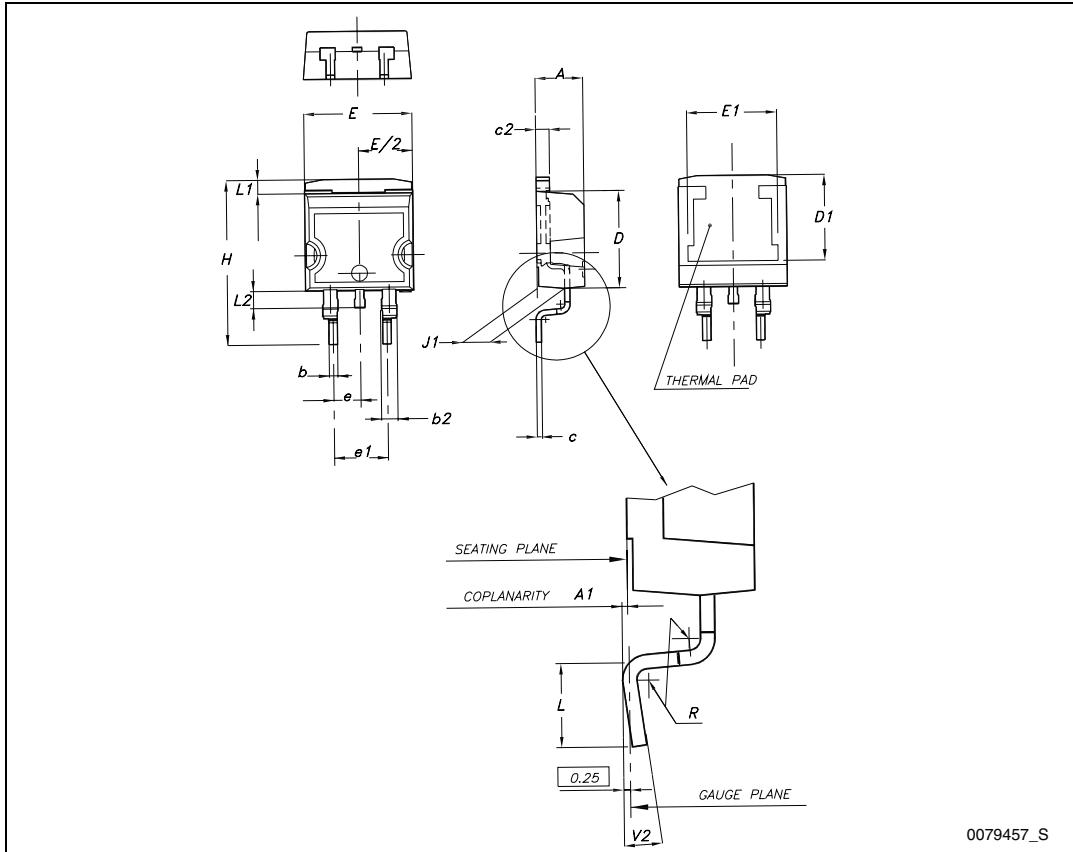


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
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Table 5. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 6. D²PAK (TO-263) drawing

4 Revision history

Table 6. Document revision history

Date	Revision	Changes
23-Jan-2012	1	Initial release.

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